

### ● General Description

The AGM30P08A combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

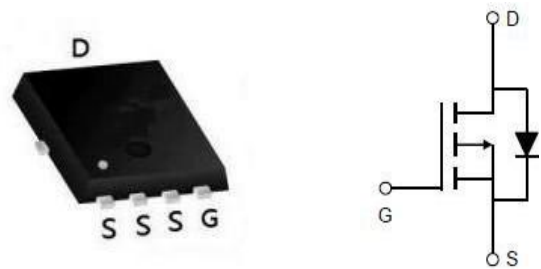
### ● Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

### Product Summary

BVDSS	RDSON	ID
-30V	7.0mΩ	-60A

### PDFN5\*6 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM30P08A	AGM30P08A	PDFN5*6	330mm	12mm	3000

**Table 1. Absolute Maximum Ratings (TA=25°C)**

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-30	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) <b>(Note 1)</b>	-60	A
	Drain Current-Continuous(Tc=100°C)	-39	A
IDM (pulse)	Drain Current-Continuous@ Current-Pulsed <b>(Note 2)</b>	-240	A
PD	Maximum Power Dissipation(Tc=25°C)	60	w
	Maximum Power Dissipation(Tc=100°C)	23.8	w
EAS	Avalanche energy <b>(Note 3)</b>	196	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	--	°C/W
RθJC	Thermal Resistance Junction-Case <sup>1</sup>	---	2.1	°C/W

**Table 3. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

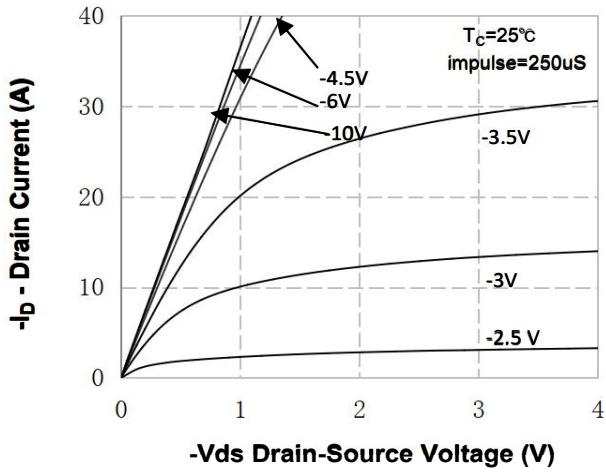
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V ID=250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	--	--	-1.0	μA
IGSS	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.6	-2.5	V
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-10A	--	20	--	S
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A	--	7.0	8.5	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	--	10.5	13	mΩ
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-30V, F=1MHZ	--	2497	--	pF
C <sub>oss</sub>	Output Capacitance		--	240	--	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	230	--	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1.0MHz	--	--	--	Ω
<b>Switching Times</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-30A, R <sub>I</sub> =3.0Ω	--	14	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	20	--	nS
t <sub>d(off)</sub>	Turn-Off Delay Time		--	56	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	48	--	nS
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-20A	--	32	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	6.6	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	8.0	--	nC
<b>Source-Drain Diode Characteristics</b>						
I <sub>SD</sub>	Source-Drain Current(Body Diode)		--	--	-60	A
V <sub>SD</sub>	Forward on Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-15A	--	--	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-15A ,	--	--	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=-500A/μs , T <sub>J</sub> =25°C	--	--	--	nc

Notes 1.The maximum current rating is package limited.

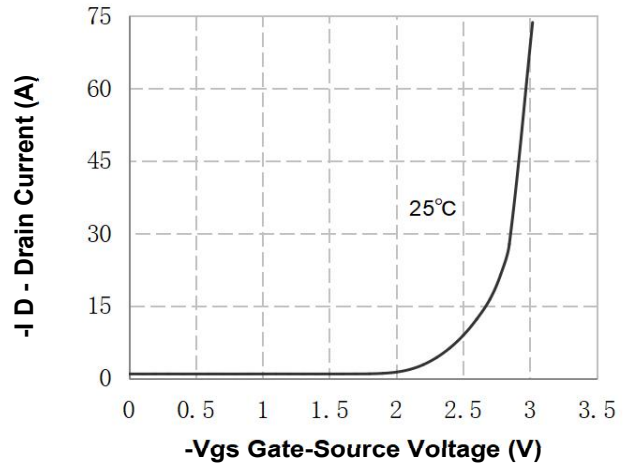
Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T<sub>J</sub>=25°C

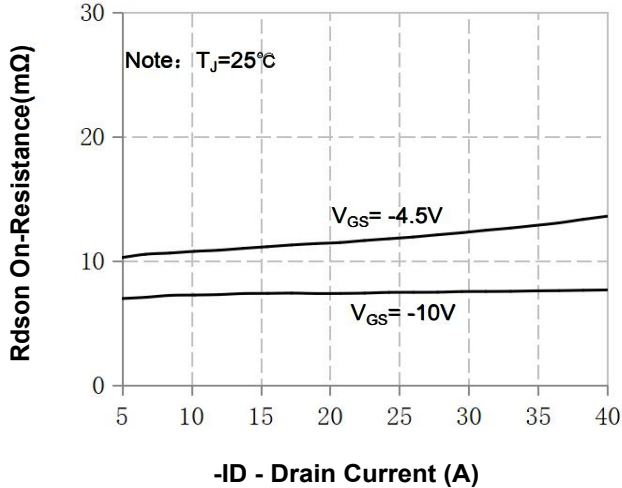
**P- Channel Typical Characteristics**



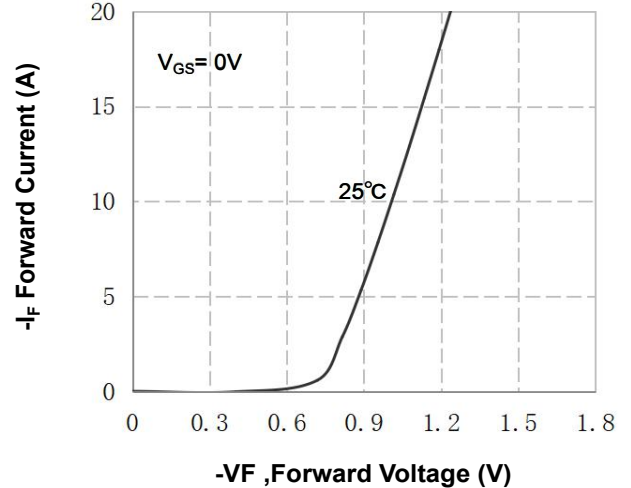
**Figure 1. On-Region Characteristics**



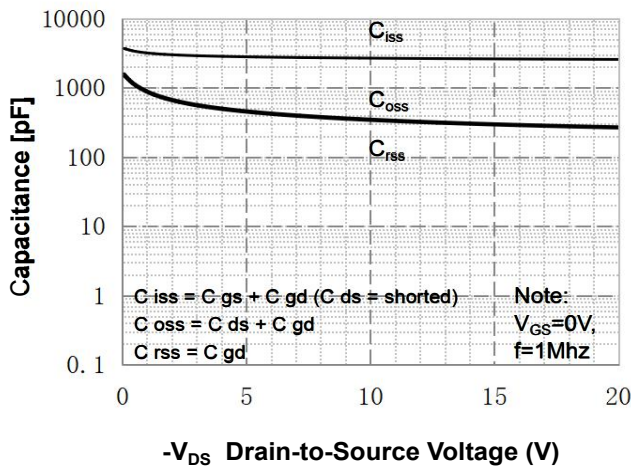
**Figure 2. Transfer Characteristics**



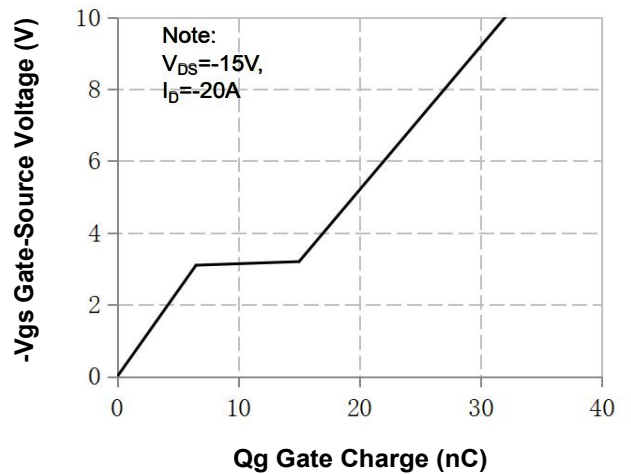
**Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**

P- Channel Typical Characteristics (Continued)

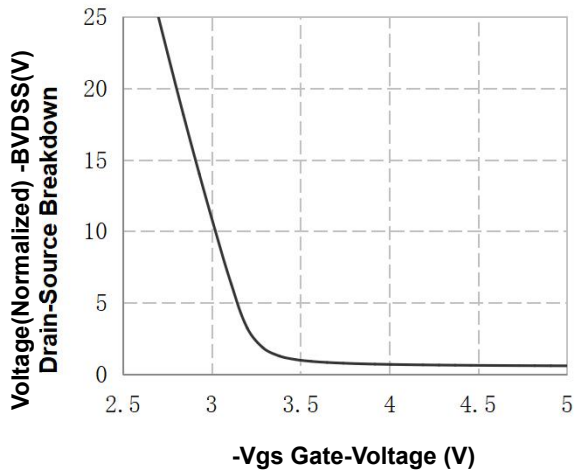


Figure 7. Breakdown Voltage Variation vs Gate-Voltage

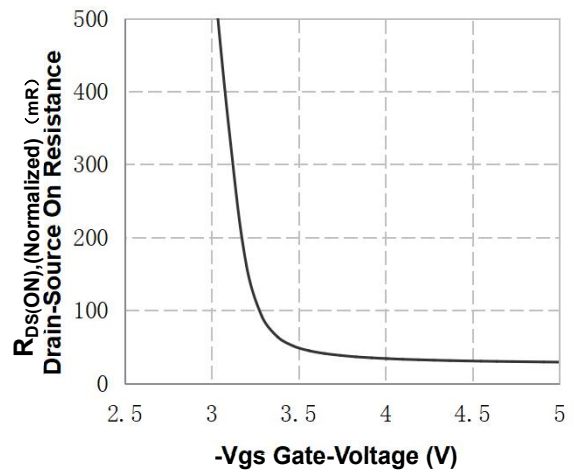


Figure 8. On-Resistance Variation vs Gate Voltage

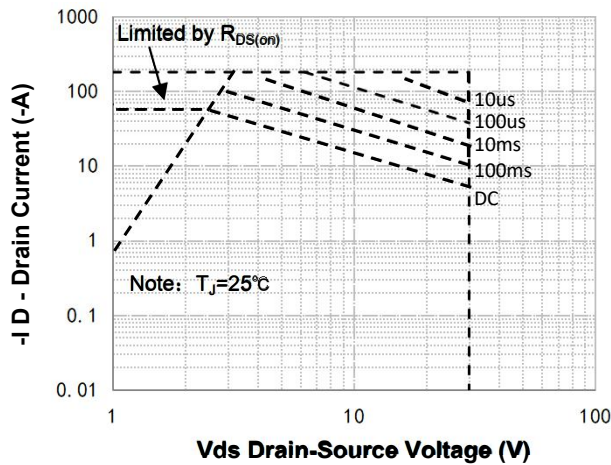


Figure 9. Maximum Safe Operating Area

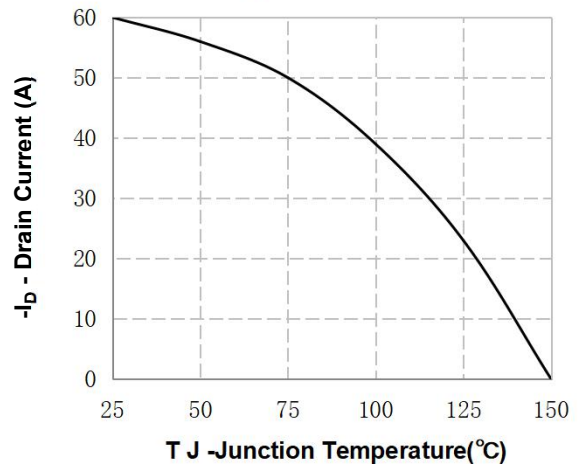


Figure 10. Maximum PContinuous Drain Current vs Case Temperature

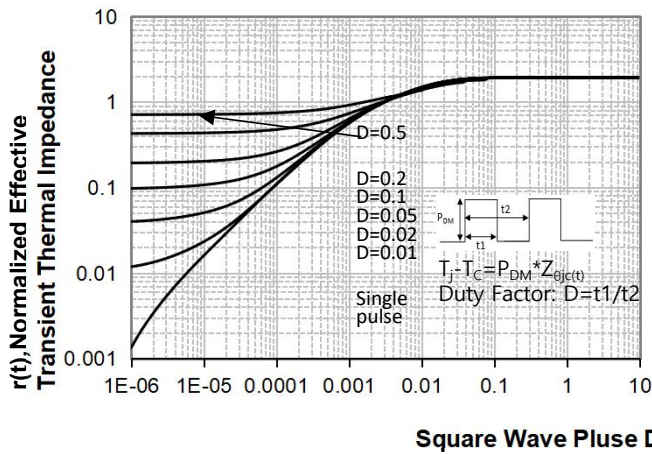
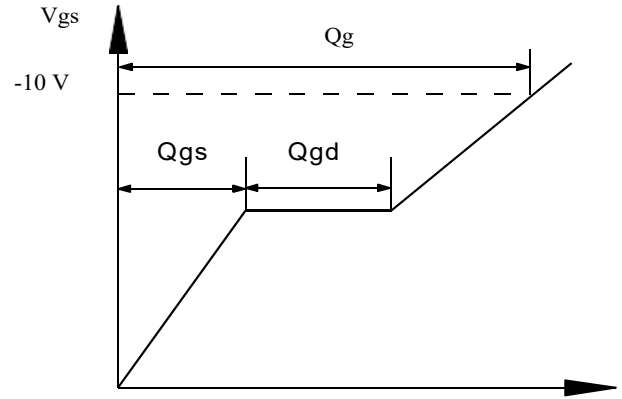
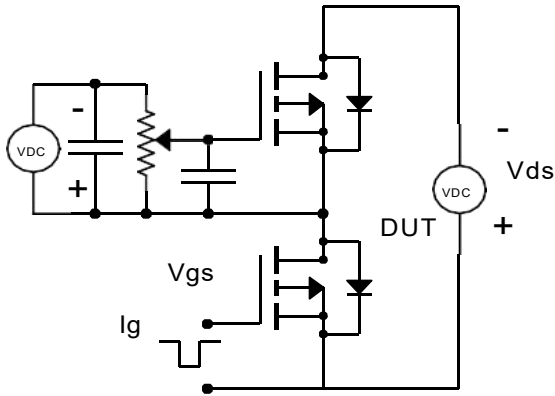
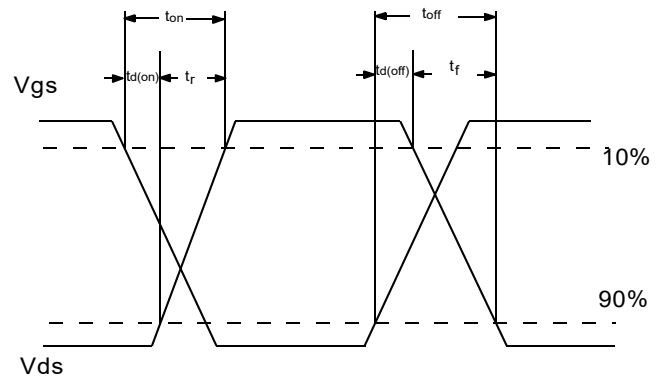
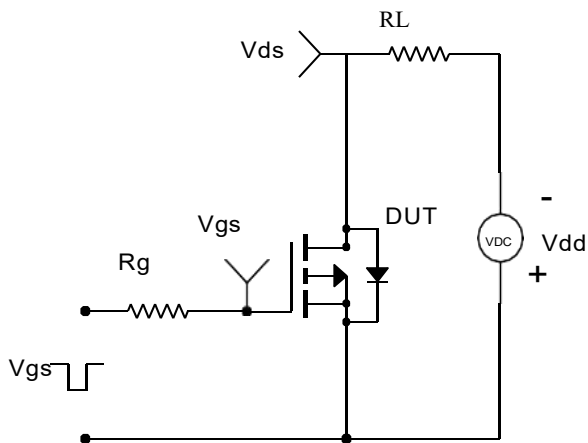


Figure 11. Transient Thermal Response Curve

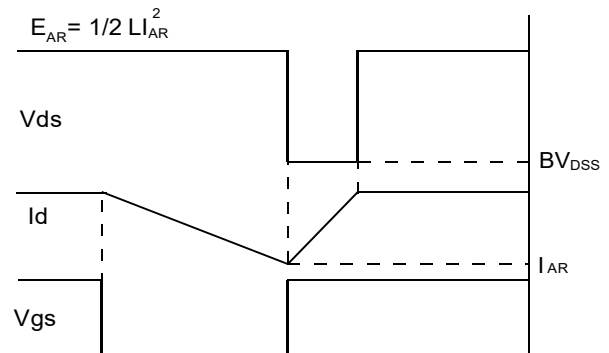
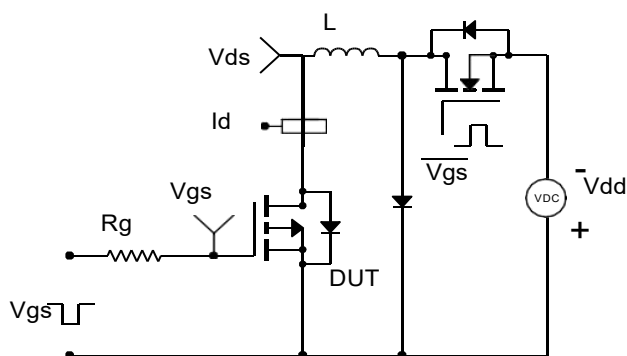
### Gate Charge Test Circuit & Waveform



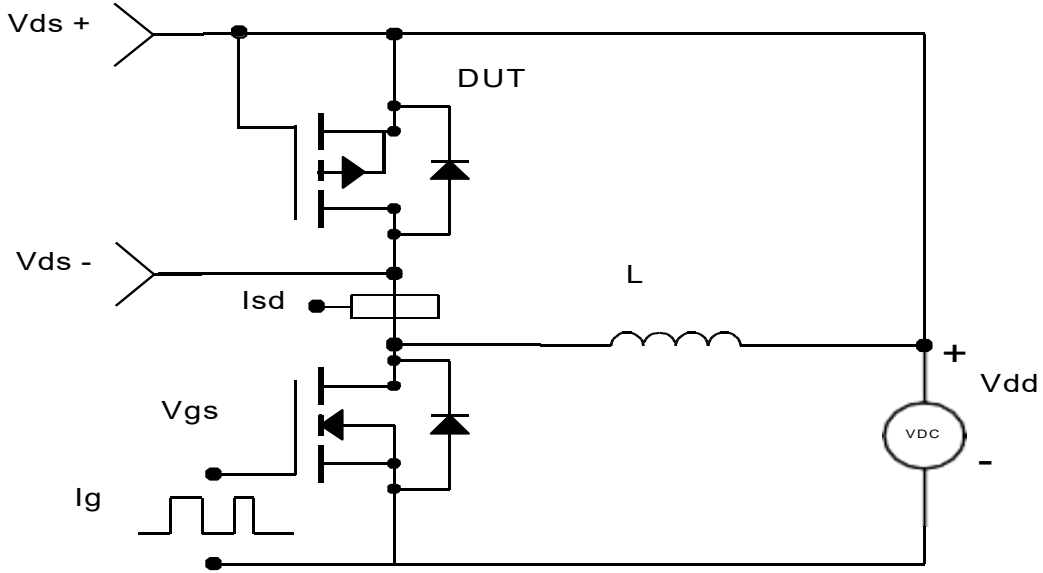
### Resistive Switching Test Circuit & Waveforms



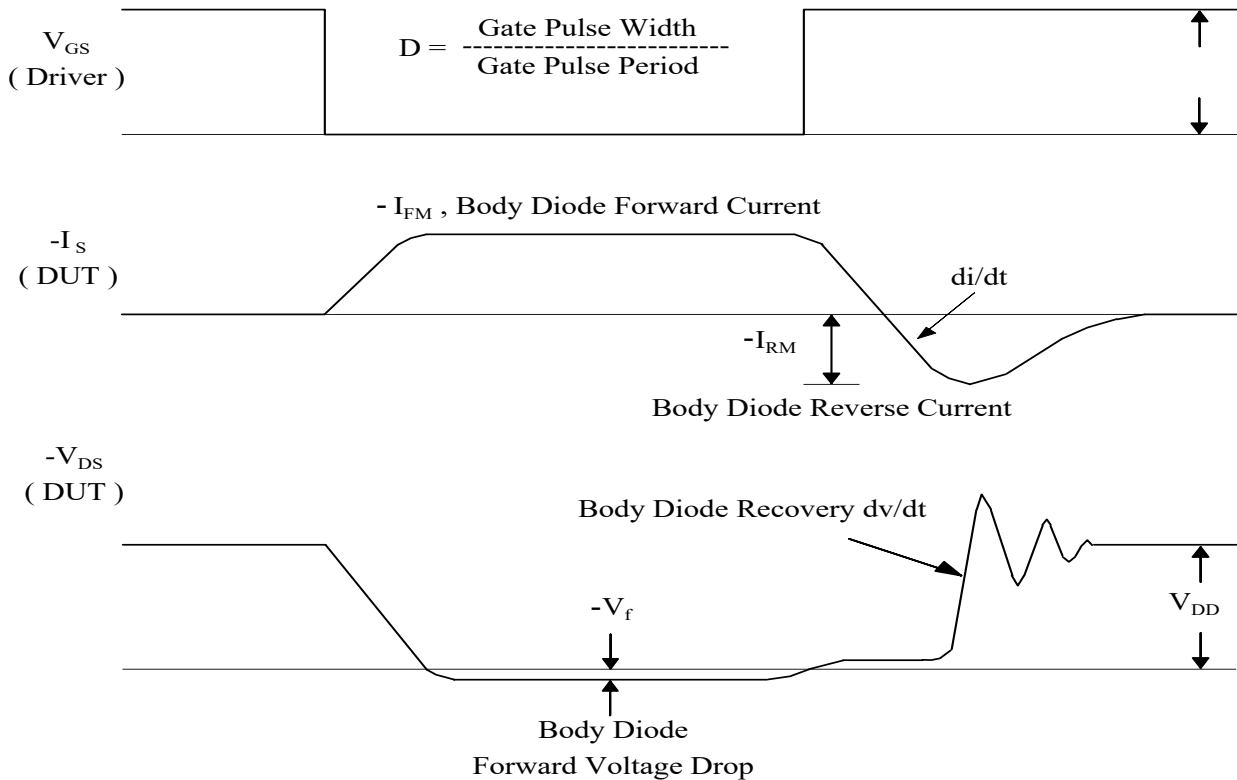
### Unclamped Inductive Switching Test Circuit & Waveforms

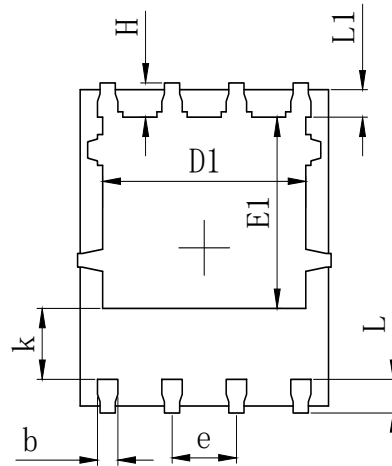
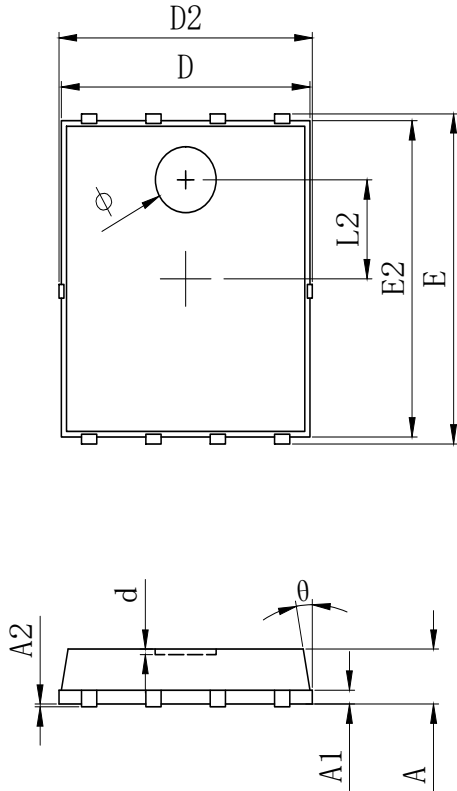


## Peak Diode Recovery $dv/dt$ Test Circuit & Waveforms

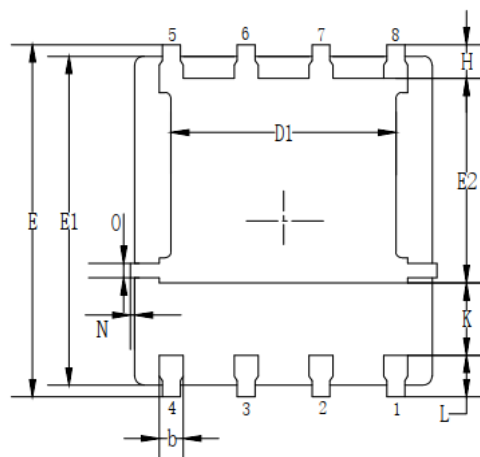
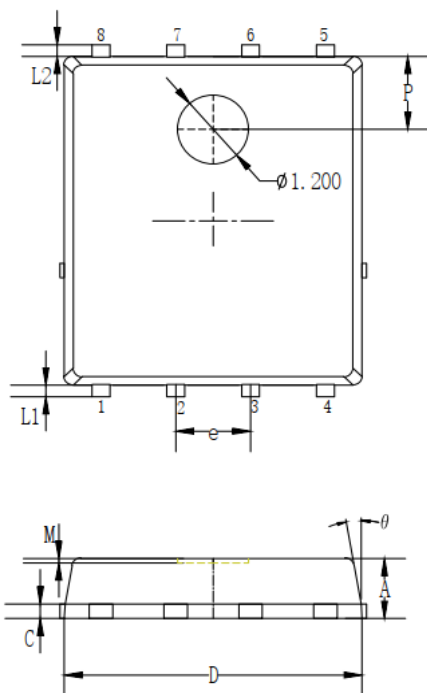


- $dv/dt$  controlled by  $R_G$
- $I_{SD}$  controlled by pulse period



**•Dimensions (PDFN5\*6)**


SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0°0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
φ	1.100	1.200	1.300
d			0.100



Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		


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